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PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.: 6,828,235 B2

Issue Date: December 7, 2004

Inventor(s): Satoshi TAKANO

Title: SEMICONDUCTOR MANUFACTURING METHOD, SUBSTRATE
PROCESSING METHOD, AND SEMICONDUCTOR MANUFACTURING
APPARATUS

Docket No.: 109107

REQUEST FOR CERTIFICATE OF CORRECTION UNDER RULE 322

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate
MAR 15 2005
of Correction

Sir:

It is respectfully requested that a Certificate of Correction be issued in order to correct the error specified in the attached copy of Certificate of Correction Form PTO-1050.

It is believed that the errors are on the part of the Patent and Trademark Office, and therefore no fee is due in relation to this matter in accordance with the provisions of 37 C.F.R. §1.322. However, should any fee be due, please charge the same against Deposit Account No. 15-0461 in order to ensure prompt issuance of a Certificate of Correction.

Respectfully submitted,

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Date: March 10, 2005

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DEPOSIT ACCOUNT USE
AUTHORIZATION
Please grant any extension
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MAR 16 2005

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(Also Form PTO-1050)

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO : 6,828,235 B2
DATED : December 7, 2004
INVENTOR(S) : Satoshi TAKANO

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

IN THE CLAIMS:

Please amend claim 9 as follows:

9. A substrate processing method, comprising
- a first step of carrying a substrate into a preliminary chamber from an external part;
 - a second step of continuously supplying and exhausting an inert gas to and from said preliminary chamber at least from a time before opening a first ~~sate~~gate between said preliminary chamber and a transfer chamber, after the substrate is carried into said preliminary chamber;
 - a third step of transferring said substrate to said transfer chamber from said preliminary chamber, in a state in which the inert gas is continuously supplied and exhausted to and from said preliminary chamber and said transfer chamber, after said first gate valve is opened;
 - a fourth step of transferring said substrate to a process chamber from said transfer chamber in a state in which the inert gas is continuously supplied and exhausted to and from said transfer chamber and said process chamber, after a second gate valve between said transfer chamber and said process chamber is opened; and
 - a fifth step of subjecting said substrate to predetermine processing in said process chamber.

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PATENT NO. 6,828,235 B2

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IN THE CLAIMS:

Please amend claim 9 as follows:

9. A substrate processing method, comprising
- a first step of carrying a substrate into a preliminary chamber from an external part;
 - a second step of continuously supplying and exhausting an inert gas to and from said preliminary chamber at least from a time before opening a first ~~sate~~gate between said preliminary chamber and a transfer chamber, after the substrate is carried into said preliminary chamber;
 - a third step of transferring said substrate to said transfer chamber from said preliminary chamber, in a state in which the inert gas is continuously supplied and exhausted to and from said preliminary chamber and said transfer chamber, after said first gate valve is opened;
 - a fourth step of transferring said substrate to a process chamber from said transfer chamber in a state in which the inert gas is continuously supplied and exhausted to and from said transfer chamber and said process chamber, after a second gate valve between said transfer chamber and said process chamber is opened; and
 - a fifth step of subjecting said substrate to predetermine processing in said process chamber.

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